

# Thyristor Module

$$V_{RRM} = 2 \times 1400 \text{ V}$$

$$I_{TAV} = 220 \text{ A}$$

$$V_T = 0,97 \text{ V}$$

Phase leg

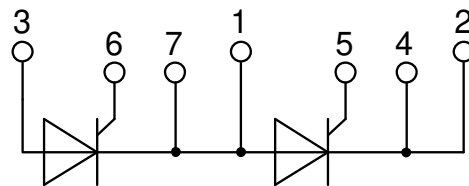
Part number

**MCC225-14io1**



Backside: isolated

 E72873



## Features / Advantages:

- International standard package
- Direct copper bonded Al<sub>2</sub>O<sub>3</sub>-ceramic with copper base plate
- Planar passivated chip
- Keyed gate/cathode twin pins

## Applications:

- Motor control, softstarter
- Power converter
- Heat and temperature control for industrial furnaces and chemical processes
- Lighting control
- Solid state switches

## Package: Y1

- Isolation Voltage: 4800 V~
- Industry standard outline
- RoHS compliant
- Soldering pins for PCB mounting
- Base plate: Copper internally DCB isolated
- Advanced power cycling

## Disclaimer Notice

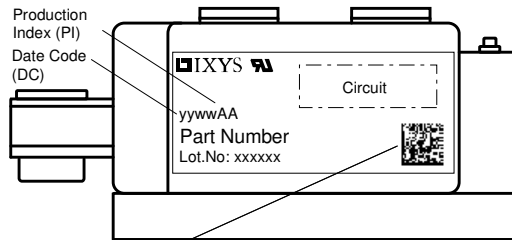
Information furnished is believed to be accurate and reliable. However, users should independently evaluate the suitability of and test each product selected for their own applications. Littelfuse products are not designed for, and may not be used in, all applications. Read complete Disclaimer Notice at [www.littelfuse.com/disclaimer-electronics](http://www.littelfuse.com/disclaimer-electronics).



Rectifier			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
$V_{RSM/DSM}$	max. non-repetitive reverse/forward blocking voltage	$T_{VJ} = 25^{\circ}C$			1500	V
$V_{RRM/DRM}$	max. repetitive reverse/forward blocking voltage	$T_{VJ} = 25^{\circ}C$			1400	V
$I_{RD}$	reverse current, drain current	$V_{R/D} = 1400 V$	$T_{VJ} = 25^{\circ}C$		1	mA
		$V_{R/D} = 1400 V$	$T_{VJ} = 125^{\circ}C$		40	mA
$V_T$	forward voltage drop	$I_T = 200 A$	$T_{VJ} = 25^{\circ}C$		1,04	V
		$I_T = 400 A$			1,18	V
		$I_T = 200 A$	$T_{VJ} = 125^{\circ}C$		0,97	V
		$I_T = 400 A$			1,14	V
$I_{TAV}$	average forward current	$T_C = 85^{\circ}C$	$T_{VJ} = 140^{\circ}C$		220	A
$I_{T(RMS)}$	RMS forward current	180° sine			400	A
$V_{T0}$	threshold voltage	} for power loss calculation only	$T_{VJ} = 140^{\circ}C$		0,79	V
$r_T$	slope resistance				0,83	mΩ
$R_{thJC}$	thermal resistance junction to case				0,157	K/W
$R_{thCH}$	thermal resistance case to heatsink			0,04		K/W
$P_{tot}$	total power dissipation		$T_C = 25^{\circ}C$		730	W
$I_{TSM}$	max. forward surge current	$t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}$	$T_{VJ} = 45^{\circ}C$		8,00	kA
		$t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{ sine}$	$V_R = 0 V$		8,64	kA
		$t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}$	$T_{VJ} = 140^{\circ}C$		6,80	kA
		$t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{ sine}$	$V_R = 0 V$		7,35	kA
$I^2t$	value for fusing	$t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}$	$T_{VJ} = 45^{\circ}C$		320,0	kA <sup>2</sup> s
		$t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{ sine}$	$V_R = 0 V$		310,5	kA <sup>2</sup> s
		$t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}$	$T_{VJ} = 140^{\circ}C$		231,2	kA <sup>2</sup> s
		$t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{ sine}$	$V_R = 0 V$		224,4	kA <sup>2</sup> s
$C_J$	junction capacitance	$V_R = 400V \quad f = 1 \text{ MHz}$	$T_{VJ} = 25^{\circ}C$		366	pF
$P_{GM}$	max. gate power dissipation	$t_p = 30 \mu s$	$T_C = 140^{\circ}C$		120	W
		$t_p = 500 \mu s$			60	W
$P_{GAV}$	average gate power dissipation				20	W
$(di/dt)_{cr}$	critical rate of rise of current	$T_{VJ} = 140^{\circ}C; f = 50 \text{ Hz}$ repetitive, $I_T = 660 A$			100	A/μs
		$t_p = 200 \mu s; di_G/dt = 1 A/\mu s;$ $I_G = 1 A; V_D = \frac{2}{3} V_{DRM}$ non-repet., $I_T = 220 A$			500	A/μs
$(dv/dt)_{cr}$	critical rate of rise of voltage	$V_D = \frac{2}{3} V_{DRM}$ $R_{GK} = \infty; \text{ method 1 (linear voltage rise)}$	$T_{VJ} = 140^{\circ}C$		1000	V/μs
$V_{GT}$	gate trigger voltage	$V_D = 6 V$	$T_{VJ} = 25^{\circ}C$		2	V
			$T_{VJ} = -40^{\circ}C$		3	V
$I_{GT}$	gate trigger current	$V_D = 6 V$	$T_{VJ} = 25^{\circ}C$		150	mA
			$T_{VJ} = -40^{\circ}C$		220	mA
$V_{GD}$	gate non-trigger voltage	$V_D = \frac{2}{3} V_{DRM}$	$T_{VJ} = 140^{\circ}C$		0,25	V
$I_{GD}$	gate non-trigger current				10	mA
$I_L$	latching current	$t_p = 30 \mu s$	$T_{VJ} = 25^{\circ}C$		200	mA
		$I_G = 0,45 A; di_G/dt = 0,45 A/\mu s$				
$I_H$	holding current	$V_D = 6 V \quad R_{GK} = \infty$	$T_{VJ} = 25^{\circ}C$		150	mA
$t_{gd}$	gate controlled delay time	$V_D = \frac{1}{2} V_{DRM}$	$T_{VJ} = 25^{\circ}C$		2	μs
		$I_G = 1 A; di_G/dt = 1 A/\mu s$				
$t_q$	turn-off time	$V_R = 100 V; I_T = 220 A; V_D = \frac{2}{3} V_{DRM}$ $di/dt = 10 A/\mu s; dv/dt = 50 V/\mu s; t_p = 200 \mu s$	$T_{VJ} = 125^{\circ}C$		200	μs



Package Y1				Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit	
$I_{RMS}$	RMS current	per terminal			600	A	
$T_{VJ}$	virtual junction temperature		-40		140	°C	
$T_{op}$	operation temperature		-40		125	°C	
$T_{stg}$	storage temperature		-40		125	°C	
<b>Weight</b>					680	g	
$M_D$	mounting torque		4,5		7	Nm	
$M_T$	terminal torque		11		13	Nm	
$d_{Spp/App}$	creepage distance on surface   striking distance through air	terminal to terminal	16,0			mm	
$d_{Spb/Apb}$		terminal to backside	16,0			mm	
$V_{ISOL}$	isolation voltage	t = 1 second	4800			V	
		t = 1 minute	4000			V	



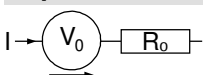
Data Matrix: part no. (1-19), DC + PI (20-25), lot.no.# (26-31), blank (32), serial no.# (33-36)

Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	MCC225-14io1	MCC225-14io1	Box	3	463574

**Equivalent Circuits for Simulation**

\* on die level

$T_{VJ} = 140^{\circ}C$

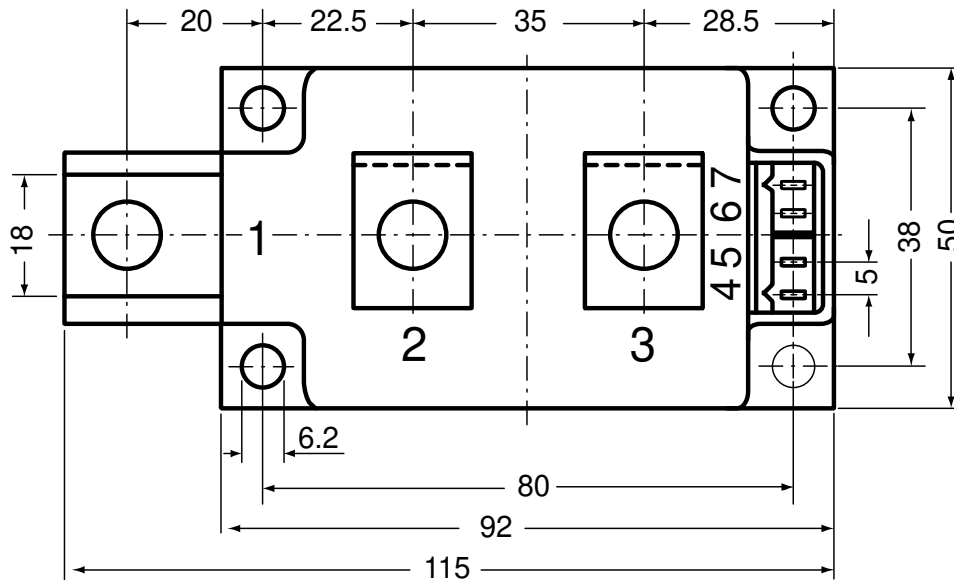
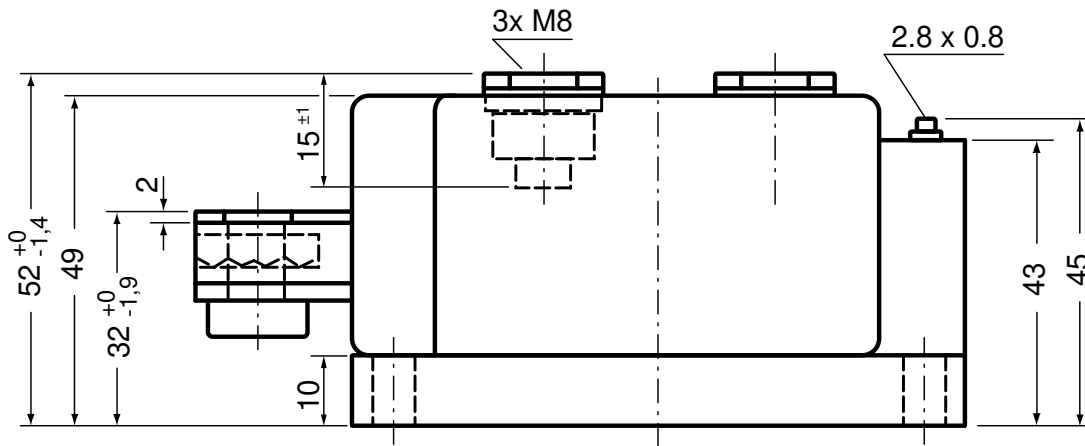


**Thyristor**

$V_{0\ max}$	threshold voltage	0,79	V
$R_{0\ max}$	slope resistance *	0,64	mΩ



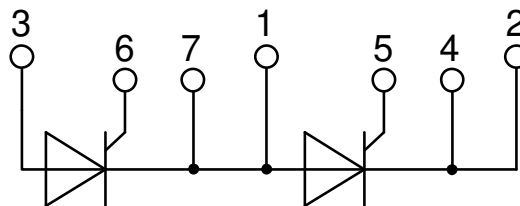
**Outlines Y1**



**Optional accessories for modules**

Keyed gate/cathode twin plugs with wire length = 350 mm, gate = white, cathode = red

Type ZY 180L (L = Left for pin pair 4/5)  
 Type ZY 180R (R = Right for pin pair 6/7) } UL 758, style 3751



**Thyristor**

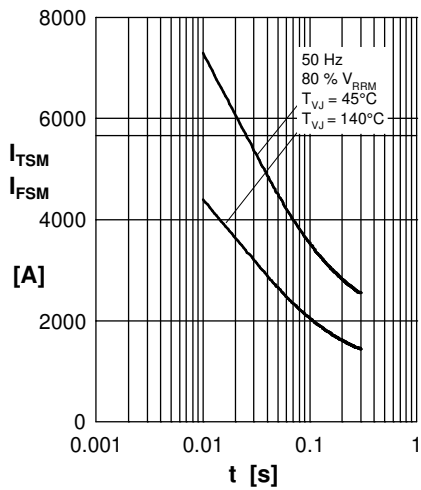


Fig. 1 Surge overload current  
 $I_{TSM/FSM}$ : Crest value,  $t$ : duration

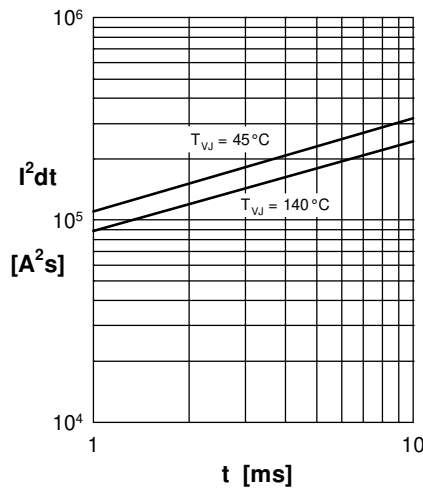


Fig. 2  $I^2dt$  versus time

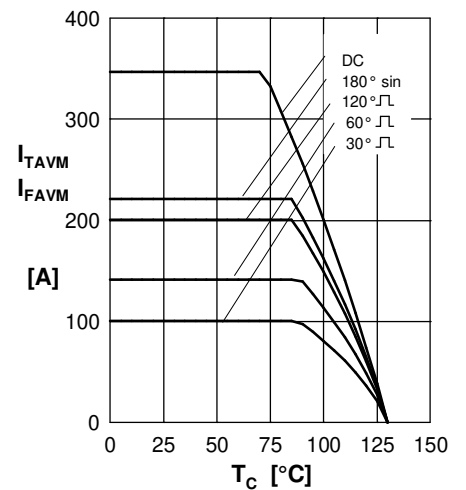


Fig. 3 Max. forward current at case temperature

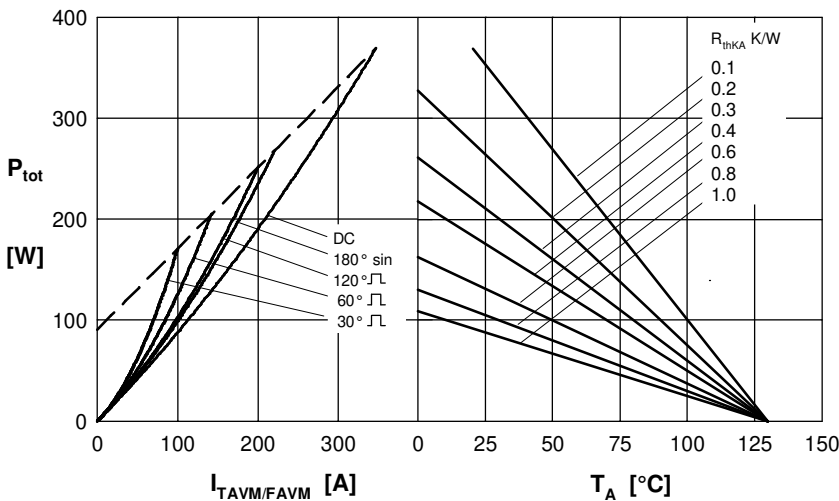


Fig. 4 Power dissipation versus on-state current and ambient temperature (per thyristor or diode)

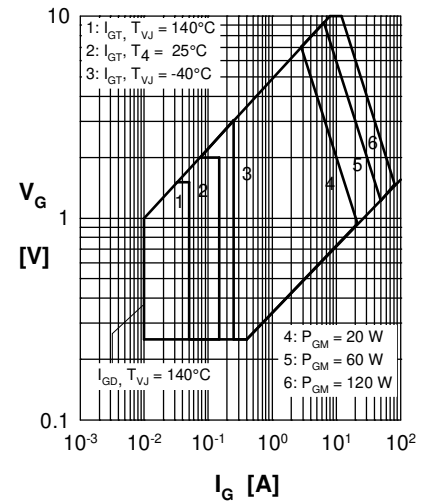


Fig. 5 Gate voltage and current

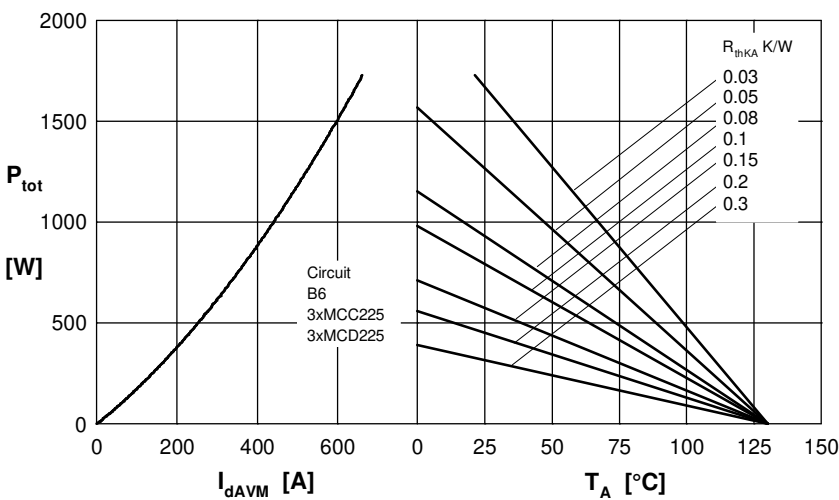


Fig. 6 Three phase rectifier bridge: Power dissipation versus direct output current and ambient temperature

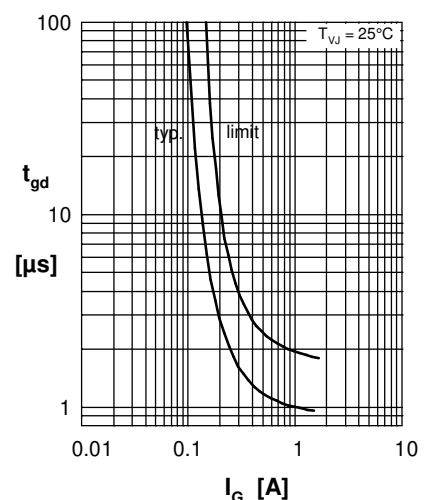


Fig. 7 Gate trigger characteristics

**Rectifier**

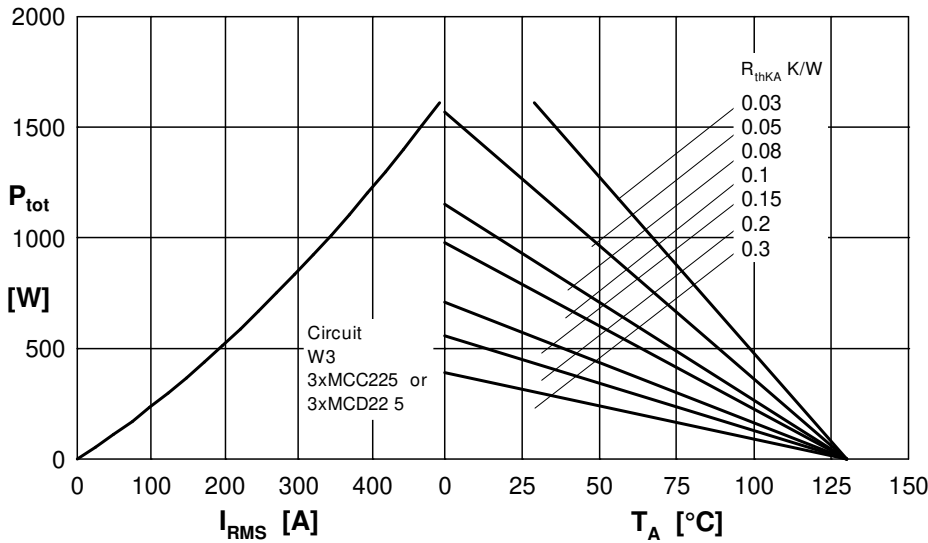


Fig. 8 Three phase AC-controller: Power dissipation versus  $R_{MS}$  output current and ambient temperature

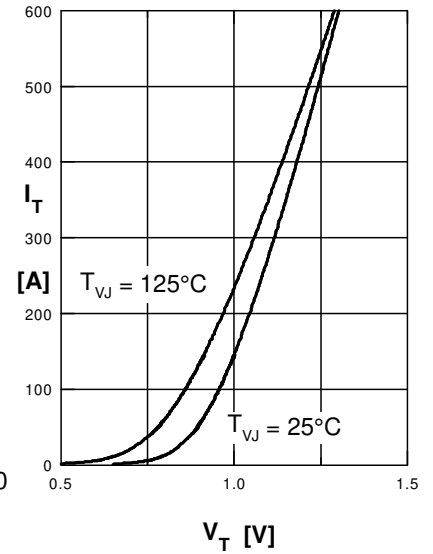


Fig. 9 Forward characteristics

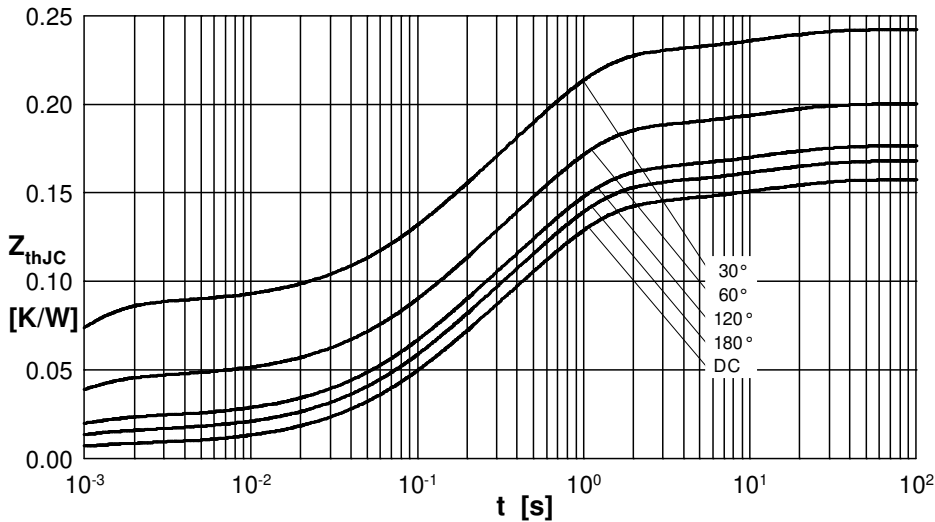


Fig. 10 Transient thermal impedance junction to case (per thyristor/diode)

$R_{thJC}$  for various conduct. angles d:

d	$R_{thJC}$ (K/W)
DC	0.157
180°	0.168
120°	0.177
60°	0.200
30°	0.243

Constants for  $Z_{thJC}$  calculation:

i	$R_{thi}$ (K/W)	t (s)
1	0.0076	0.00054
2	0.0406	0.09800
3	0.0944	0.54000
4	0.0147	12.0000

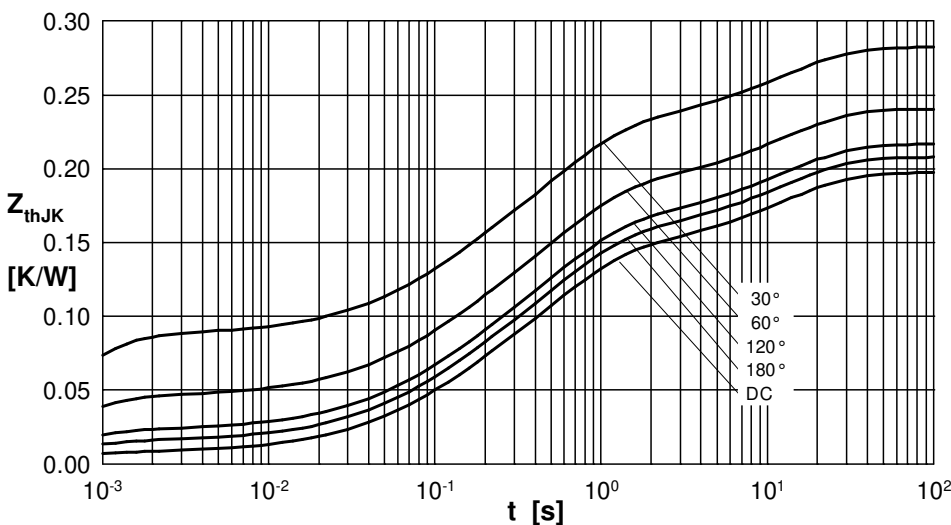


Fig. 11 Transient thermal impedance junction to heatsink (per thyristor/diode)

$R_{thJK}$  for various conduct. angles d:

d	$R_{thJK}$ (K/W)
DC	0.197
180°	0.208
120°	0.217
60°	0.240
30°	0.283

Constants for  $Z_{thJK}$  calculation:

i	$R_{thi}$ (K/W)	t (s)
1	0.0076	0.00054
2	0.0406	0.09800
3	0.0944	0.54000
4	0.0147	12.0000
5	0.0400	12.0000